



RQ1E100XN

Nch 30V 10A Power MOSFET

Datasheet

V_{DSS}	30V
$R_{DS(on)}$ (Max.)	10.5mΩ
I_D	10A
P_D	1.5W

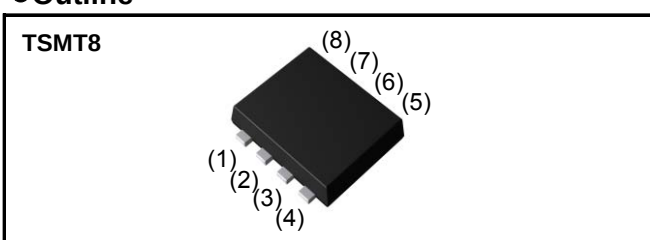
●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT8).
- 4) Pb-free lead plating ; RoHS compliant

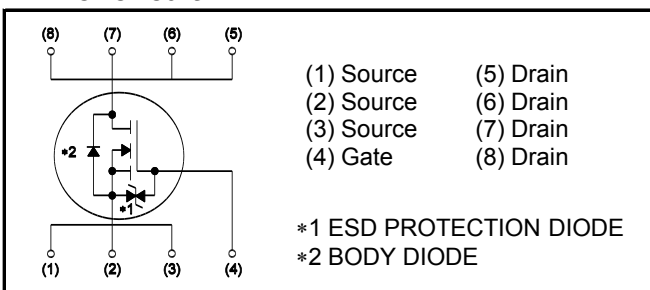
●Application

DC/DC converters

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	XS

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	30	V
Continuous drain current	I_D^{*1}	± 10	A
Pulsed drain current	$I_{D,pulse}^{*2}$	± 36	A
Gate - Source voltage	V_{GSS}	± 20	V
Power dissipation	P_D^{*3}	1.5	W
	P_D^{*4}	0.55	W
Junction temperature	T_j	150	$^\circ\text{C}$
Range of storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA}^{*3}	-	-	83.3	°C/W
Thermal resistance, junction - ambient	R_{thJA}^{*4}	-	-	227	°C/W

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	35	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	1.0	-	2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = 1mA$ referenced to 25°C	-	-3.7	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS}=10V, I_D=10A$	-	7.5	10.5	mΩ
		$V_{GS}=4.5V, I_D=10A$	-	9.5	13.3	
		$V_{GS}=4.0V, I_D=10A$	-	10.0	14.0	
		$V_{GS}=10V, I_D=10A, T_j=125^\circ\text{C}$	-	12	17	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	2	-	Ω
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_D = 10A$	4.9	15	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (20×20×0.8mm)

*5 Pulsed

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	1000	-	pF
Output capacitance	C_{oss}	$V_{DS} = 10V$	-	340	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	170	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 15V, V_{GS} = 10V$	-	12	-	ns
Rise time	t_r^{*5}	$I_D = 5A$	-	33	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 3\Omega$	-	50	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	14	-	

●Gate Charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 15V, I_D = 10A$ $V_{GS} = 5V$	-	12.7	-	nC
		$V_{DD} \approx 15V, I_D = 9A$ $V_{GS} = 10V$	-	24	-	
Gate - Source charge	Q_{gs}^{*5}	$V_{DD} \approx 15V, I_D = 10A$	-	2.6	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = 5V$	-	6.0	-	

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_a = 25^\circ\text{C}$	-	-	1.25	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0V, I_S = 10A$	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

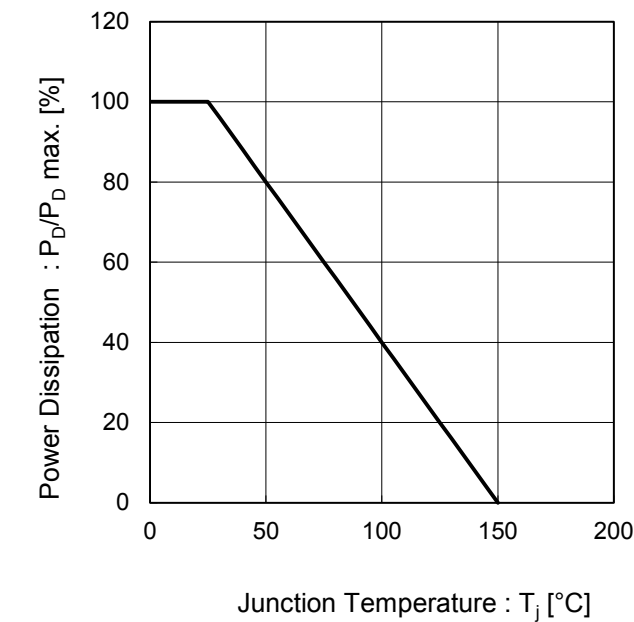


Fig.2 Maximum Safe Operating Area

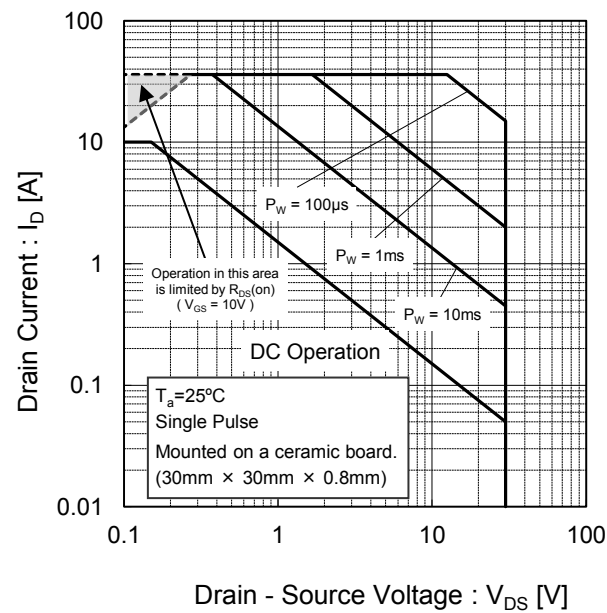


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

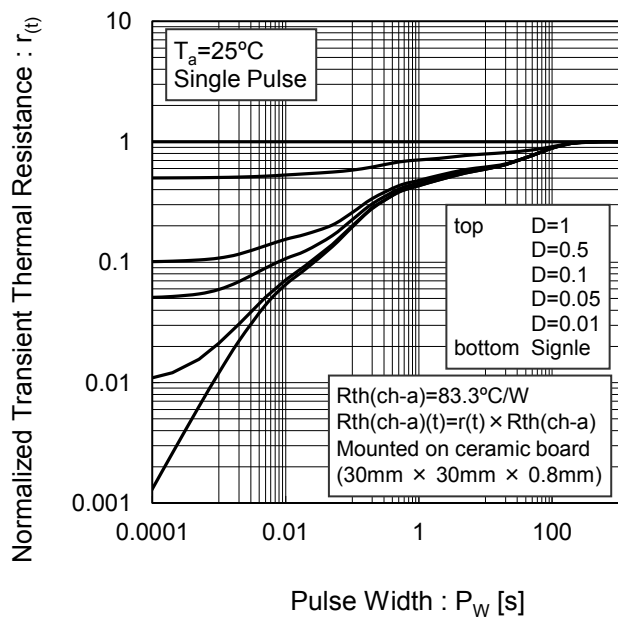
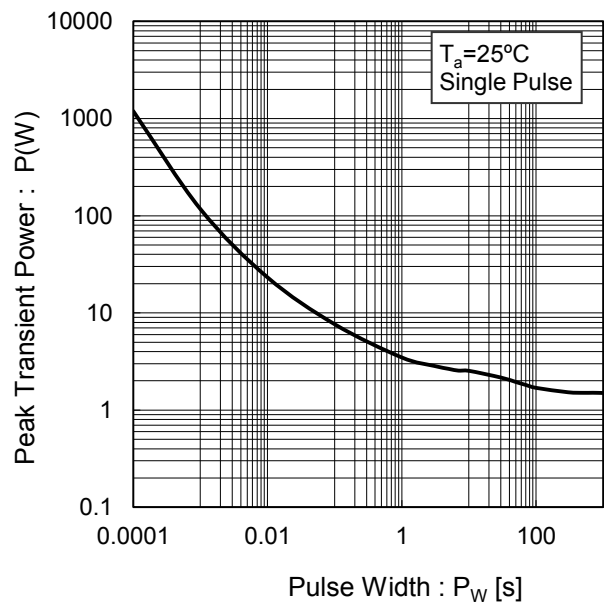


Fig.4 Single Pulse Maximum Power dissipation



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

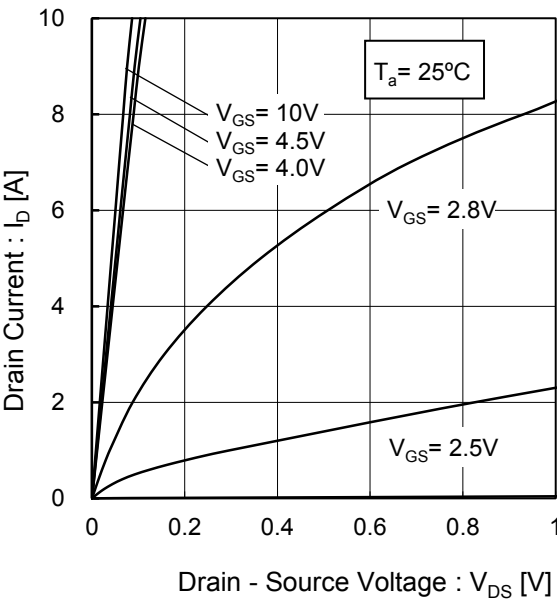
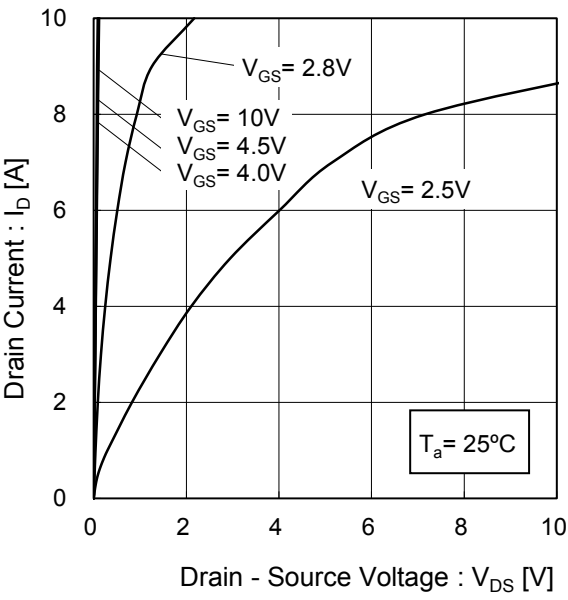


Fig.6 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.7 Breakdown Voltage
vs. Junction Temperature

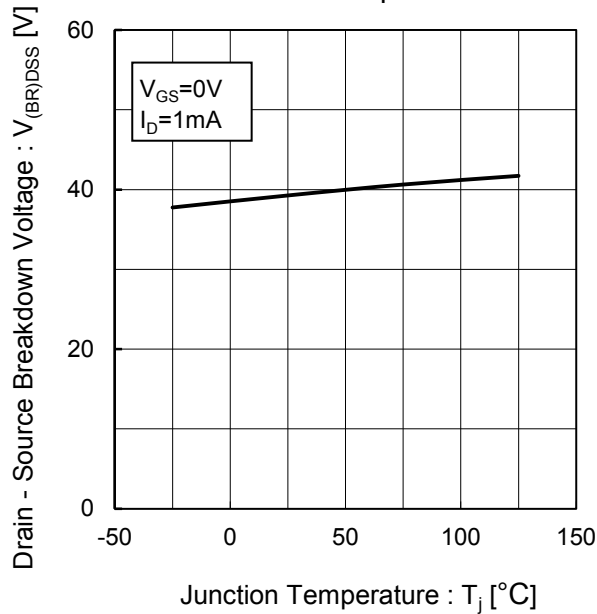


Fig.8 Typical Transfer Characteristics

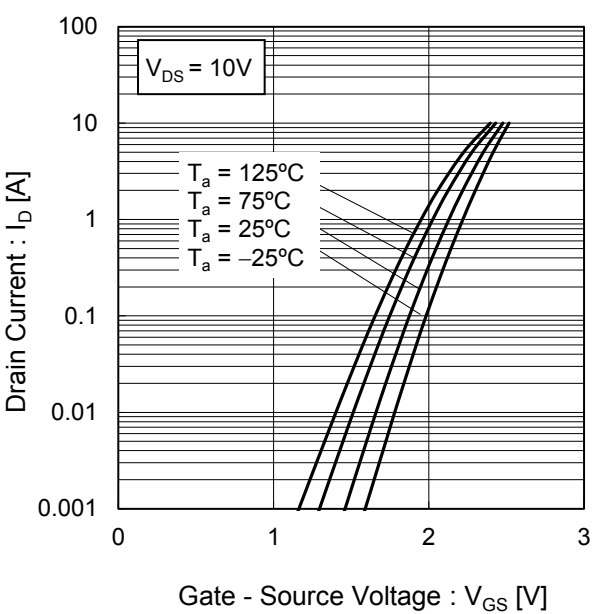


Fig.9 Gate Threshold Voltage
vs. Junction Temperature

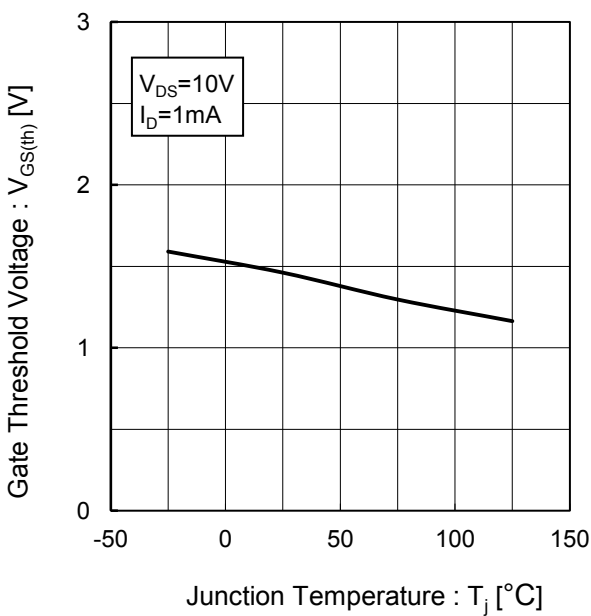
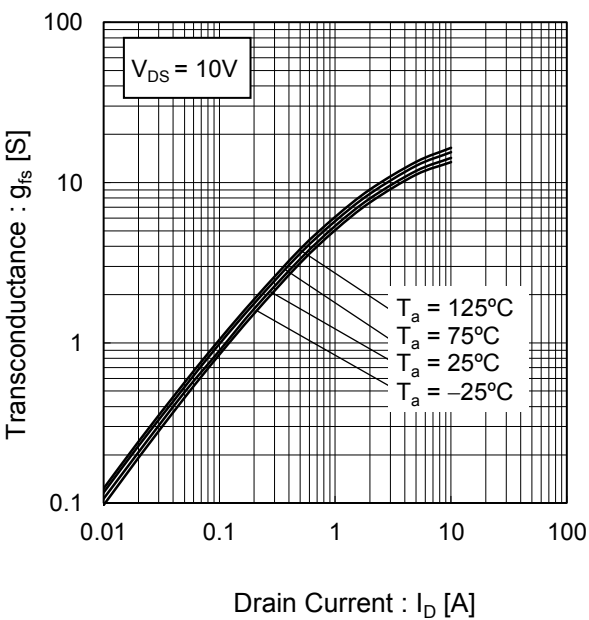


Fig.10 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.11 Drain CurrentDerating Curve

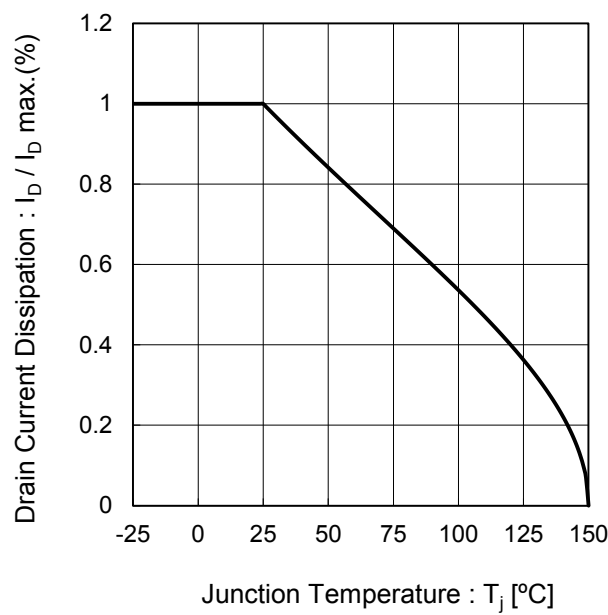


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

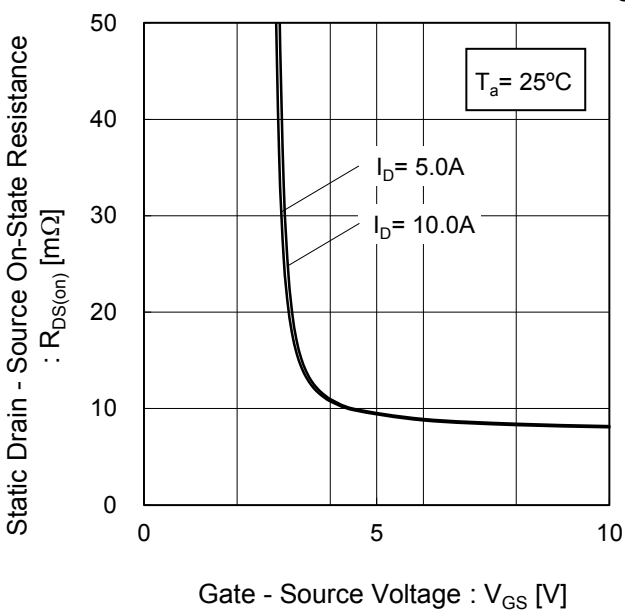


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

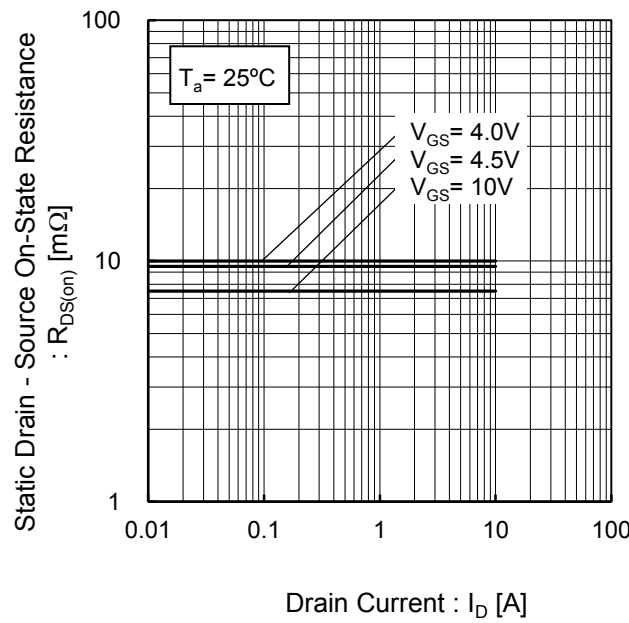
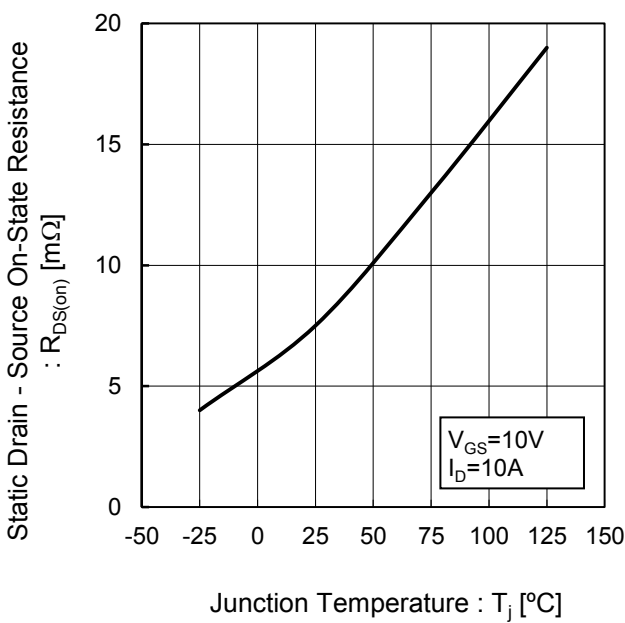


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

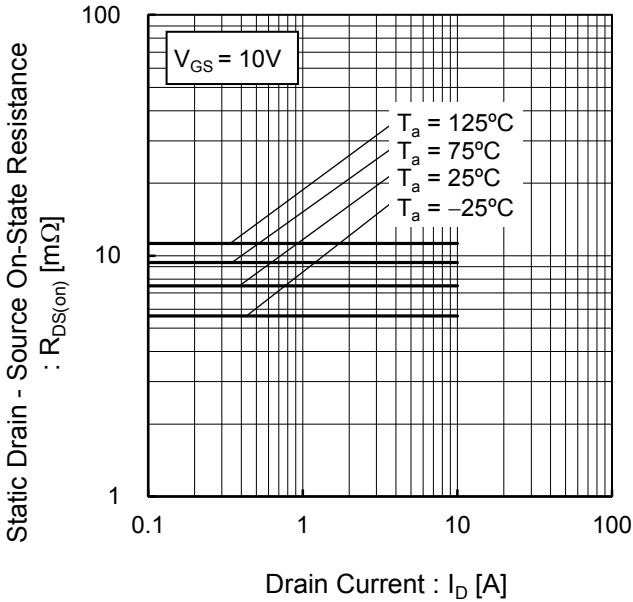


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

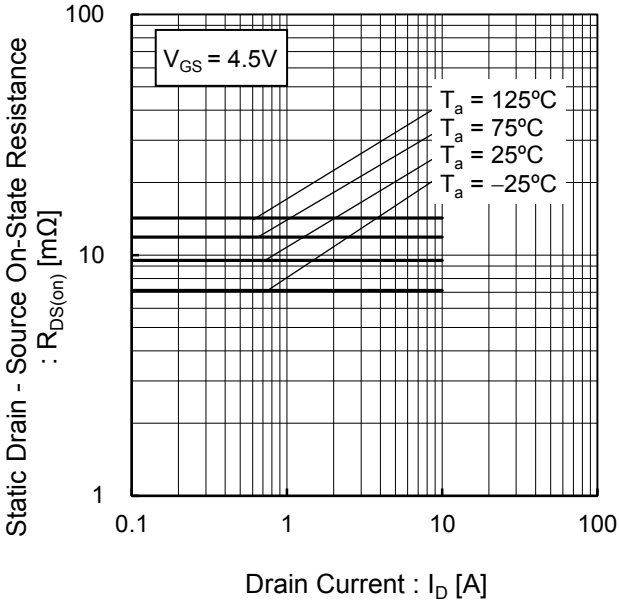
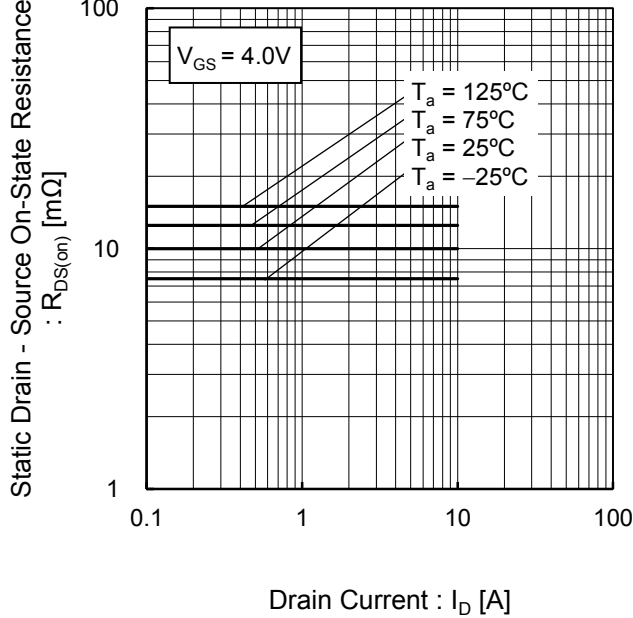


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)



●Electrical characteristic curves

Fig.18 Typical Capacitance
vs. Drain - Source Voltage

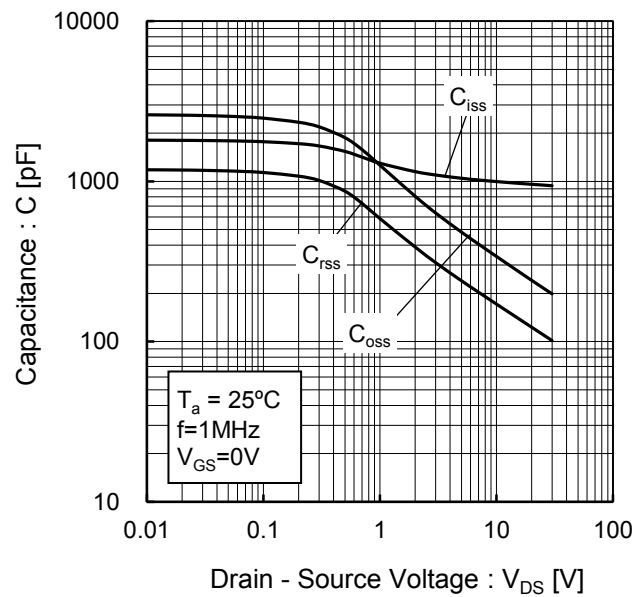


Fig.19 Switching Characteristics

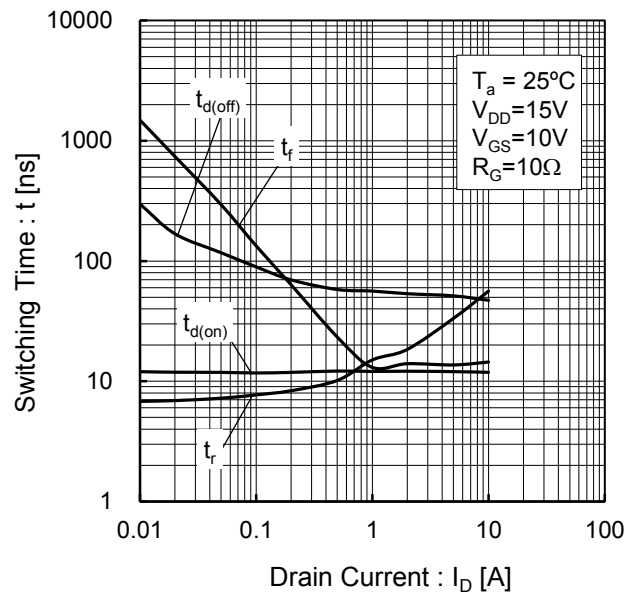


Fig.20 Dynamic Input Characteristics

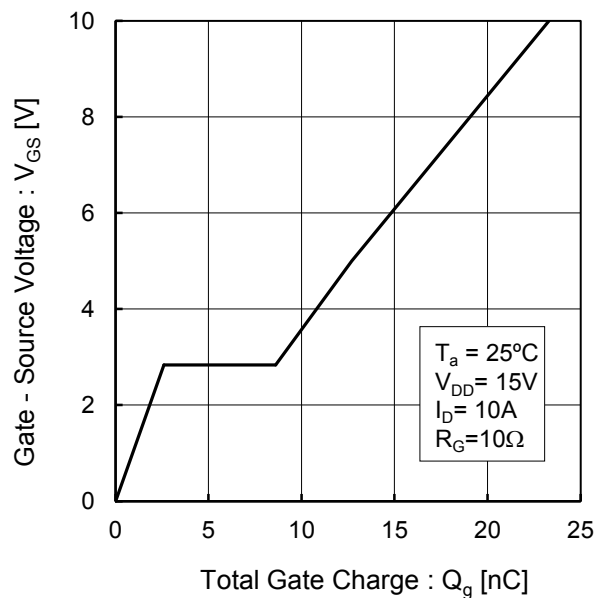
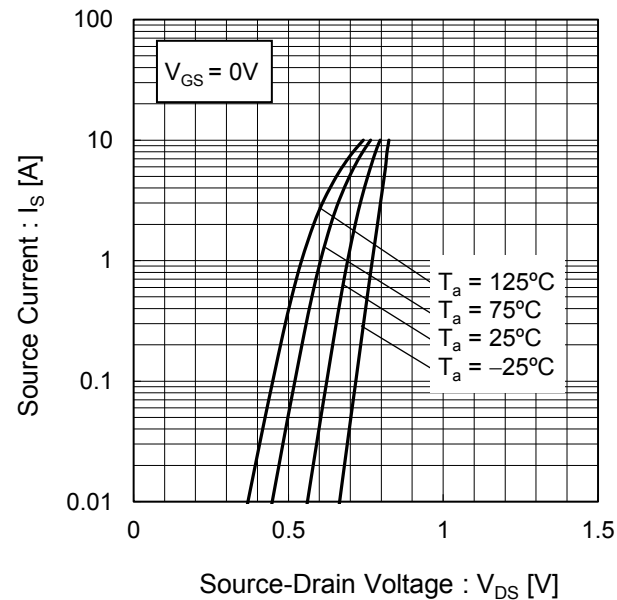


Fig.21 Source Current
vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

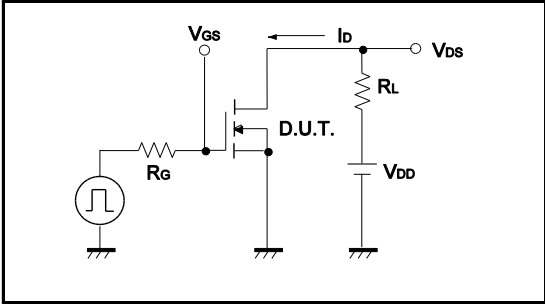


Fig.1-2 Switching Waveforms

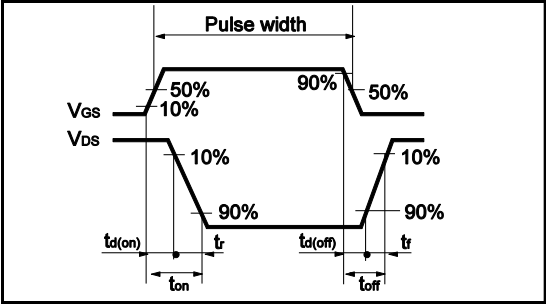


Fig.2-1 Gate Charge Measurement Circuit

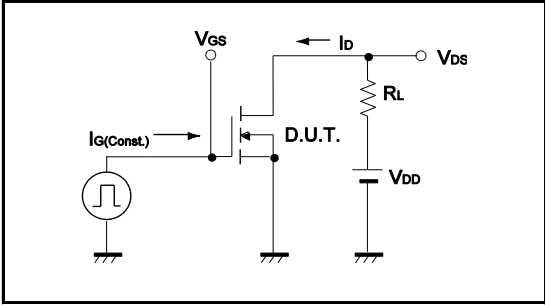
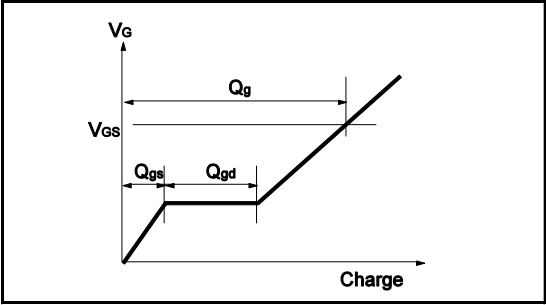
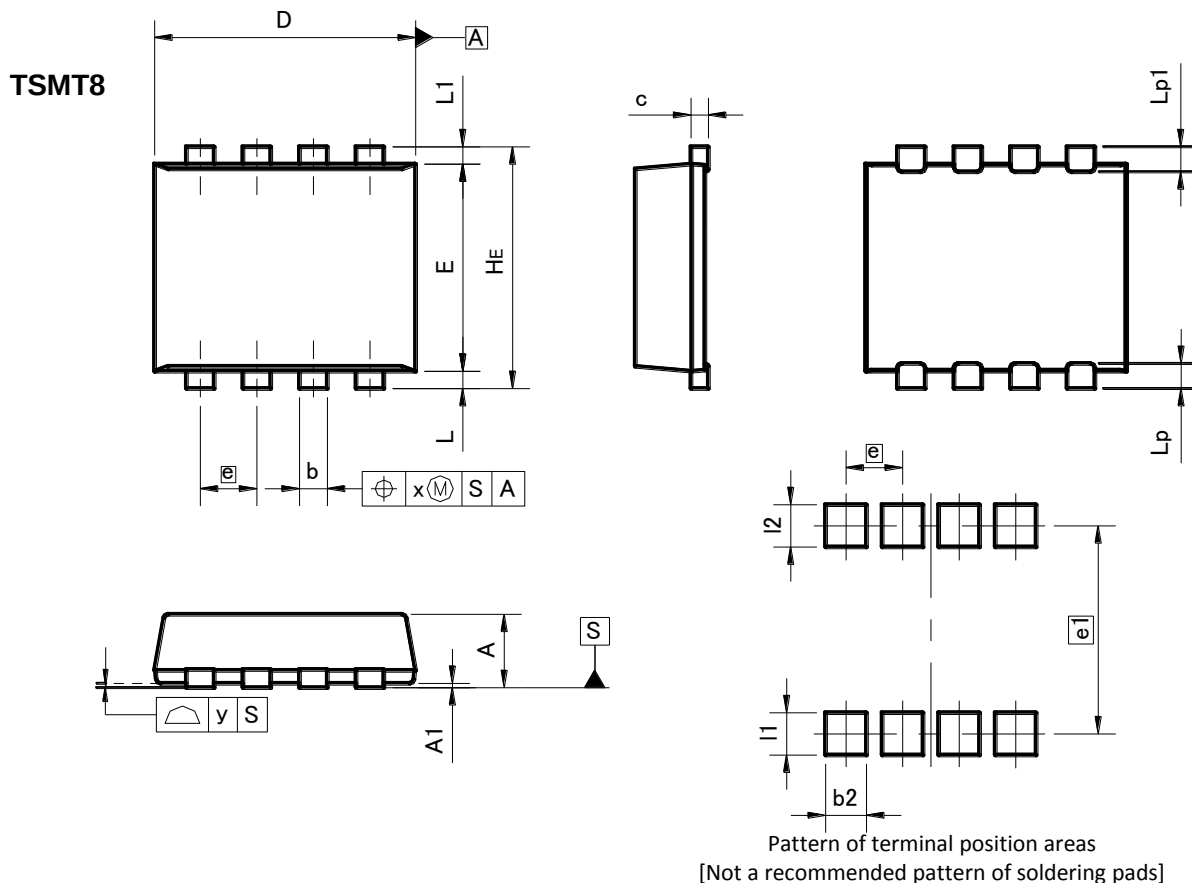


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.47	—	0.019
e1	2.41		0.095	
l1	—	0.49	—	0.019
l2	—	0.49	—	0.019

Dimension in mm / inches

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